

## IN THE CLAIMS

1 (Currently Amended). A method comprising:  
positioning a conductive surface of a semiconductor wafer on a conductive polishing pad;  
providing electrical contact of a first polarity to said surface across the pad; and  
providing electrodes in contact with said surface, said electrodes extending through said pad, said electrodes being of opposite polarity to said ~~contact~~ first polarity.

Claims 2-4 (Canceled).

5 (Previously Presented). The method of claim 1 including providing circularly shaped openings in said pad over said electrodes.

6 (Original). The method of claim 1 including positioning said pad over a conductive platen.

7 (Original). The method of claim 5 including insulating said electrode from said pad.

8 (Original). The method of claim 1 including providing said pad over a conductive platen and applying potential to said film through said pad and platen.

9 (Original). The method of claim 1 including providing electrical contact to said surface over the entire extent of said surface.

10 (Original). The method of claim 1 including applying pressure between said surface and said pad.

11 (Original). The method of claim 1 including providing an abrasive fluid between said surface and said pad.

12 (Original). The method of claim 1 including counter rotating said pad and said surface.

Claims 13-19 (Canceled).